Important Note : 1. On completing your answers, compulsorily draw diagonal cross tines on the remaining blank pages

Eighth Semester B.E. Degree Examination, June/July 2018 **Advanced Nanomaterials and Devices**

Time: 3 hrs.

Max. Marks: 100

Note: Answer FIVE full questions, selecting at least TWO questions from each part.

DADT

		PART – A	
1	a.	Explain in brief nanoporous materials. Discuss different types of nanoporous materials.	rials.
			(05 Marks)
	b.	Discuss different applications of porous structured Carbon Nano Tubes (CNTs).	(05 Marks)
	c.	Describe AgX photography with neat diagram.	(10 Marks)
2	a.	Explain electronic transport in 1, 2 and 3 dimensions.	(08 Marks)
	b.	Explain the quantum effects in quantum wires and mention their applications.	(08 Marks)
	c.	Discuss optical properties of quantum dots with example.	(04 Marks)
3	a.	Explain organic and inorganic based TFT's.	(10 Marks)
•	ö.	Write a note on Resonant Tunneling devices.	(10 Marks)
	0.	write a note on resonant runnering devices.	(IU WIAFKS)
4	a.	Mention and explain any two lithography techniques used for nanofabrication.	(10 Marks)
	b.	Explain about self assembled inorganic layers.	(10 Marks)
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PART – B			
5	a.	Describe about energy supply for molecular machines.	(05 Marks)
_	b.	Discuss in brief molecular switching. Explain in brief any one type of molecular	
	0.	12 is cass in other more called switching. Explain in other any one type of increedial	(08 Marks)
	c.	Write about molecular machines powered by light energy.	(07 Marks)
		The about motocalar macrimes portered by fight energy.	(U/ Maiks)
6	a.	Discuss about bacterial transcription and translation processes at single molecule level.	
			(12 Marks)
	b.	Explain force generation and real time dynamics.	(08 Marks)
7	a.	Discuss in brief nanoreactors. Explain molecular nanoreactors with example.	(08 Marks)
	b.	Discuss in detail nanometry of active filaments.	(12 Marks)
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8	a.	Explain in brief, Bistable systems. Explain about molecular shift register.	(12 Marks)
	b.	Write a note on fabrication and patterning of nanoscale device.	(08 Marks)
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